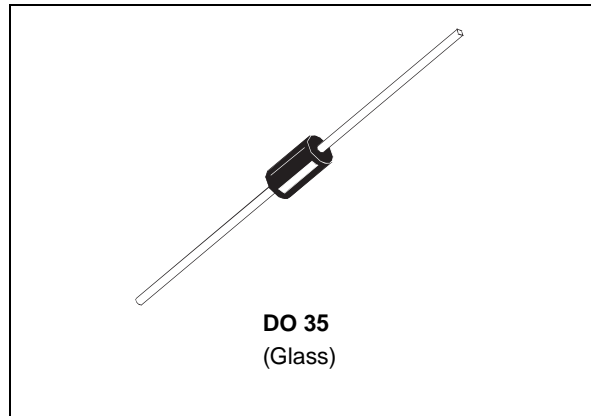


**SMALL SIGNAL SCHOTTKY DIODE****DESCRIPTION**

General purpose, metal to silicon diode featuring high breakdown voltage low turn-on voltage.

**ABSOLUTE RATINGS** (limiting values)

Symbol	Parameter	Value	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	100	V
I_F	Forward Continuous Current*	$T_a = 25\text{ °C}$ 150	mA
I_{FRM}	Repetitive Peak Forward Current*	$t_p \leq 1\text{ s}$ $\delta \leq 0.5$ 350	mA
I_{FSM}	Surge non Repetitive Forward Current*	$t_p = 10\text{ ms}$ 750	mA
P_{tot}	Power Dissipation*	$T_1 = 80\text{ °C}$ 150	mW
T_{stg} T_j	Storage and Junction Temperature Range	- 65 to + 150 - 65 to + 125	°C
T_L	Maximum Temperature for Soldering during 10s at 4mm from Case	230	°C

THERMAL RESISTANCE

Symbol	Test Conditions	Value	Unit
$R_{th(j-a)}$	Junction-ambient*	300	°C/W

* On infinite heatsink with 4mm lead length.

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ELECTRICAL CHARACTERISTICS

STATIC CHARACTERISTICS

Symbol	Test Conditions		Min.	Typ.	Max.	Unit
V_{BR}	$T_j = 25^\circ\text{C}$	$I_F = 10\mu\text{A}$	100			V
V_F^*	$T_j = 25^\circ\text{C}$	$I_F = 0.1\text{mA}$			0.25	V
	$T_j = 25^\circ\text{C}$	$I_F = 10\text{mA}$			0.45	
	$T_j = 25^\circ\text{C}$	$I_F = 250\text{mA}$			1	
I_R^*	$T_j = 25^\circ\text{C}$	$V_R = 1.5\text{V}$			0.5	μA
	$T_j = 60^\circ\text{C}$				5	
	$T_j = 25^\circ\text{C}$	$V_R = 10\text{V}$			0.8	
	$T_j = 60^\circ\text{C}$				7.5	
	$T_j = 25^\circ\text{C}$	$V_R = 50\text{V}$			2	
	$T_j = 60^\circ\text{C}$				15	
	$T_j = 25^\circ\text{C}$	$V_R = 75\text{V}$			5	
	$T_j = 60^\circ\text{C}$				20	

DYNAMIC CHARACTERISTICS

Symbol	Test Conditions		Min.	Typ.	Max.	Unit
C	$T_j = 25^\circ\text{C}$	$V_R = 0\text{V}$		10		pF
	$T_j = 25^\circ\text{C}$	$V_R = 1\text{V}$		6		

* Pulse test: $t_p \leq 300\mu\text{s}$ $\delta < 2\%$.

Fig. 1-1: Forward voltage drop versus forward current (low level, typical values)

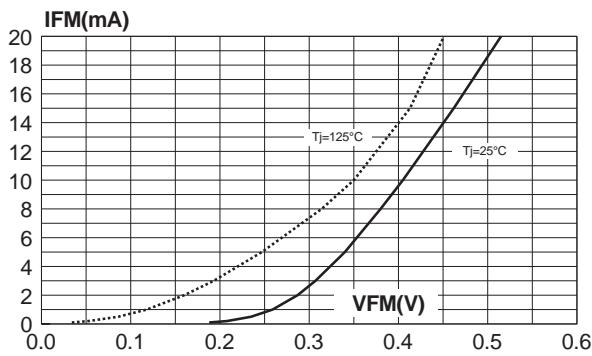


Fig. 1-2: Forward voltage drop versus forward current (high level, typical values)

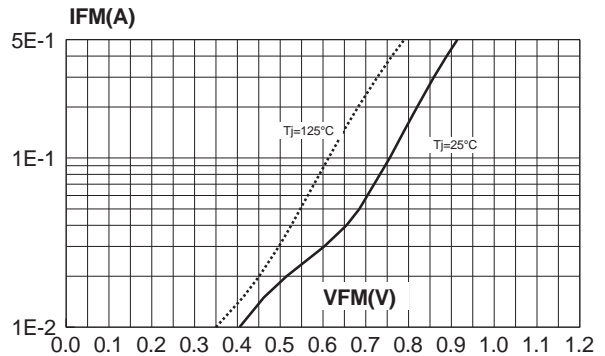


Fig. 2: Leakage current versus reverse voltage applied (typical values)

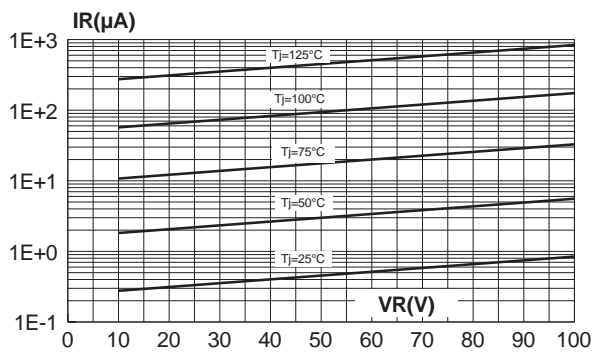


Fig. 3: Leakage current versus junction temperature (typical values)

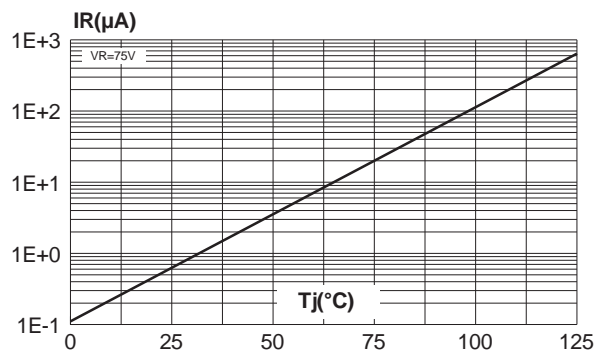
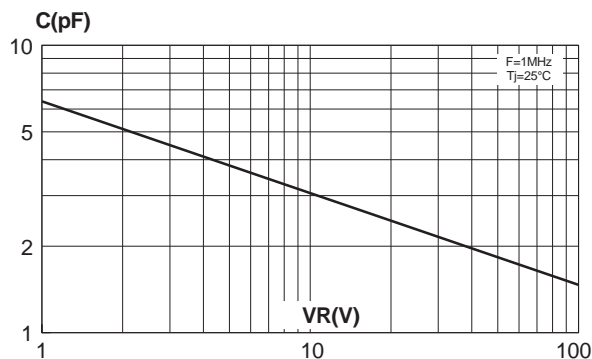


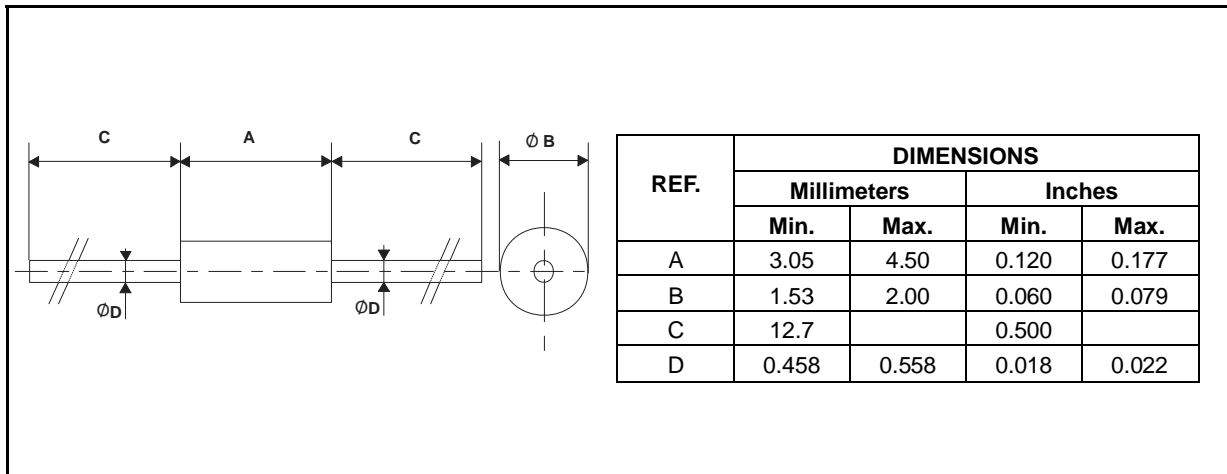
Fig. 4: Junction capacitance versus reverse voltage applied (typical values)



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PACKAGE MECHANICAL DATA

DO 35 Glass



Cooling method : by convection and conduction
Marking: clear, ring at cathode end.
Weight: 0.15g

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